b) Amendments to the Claims:

Kindly cancel claim 27 without prejudice or disclaimer.

Please amend claims 1, 11, 12 and 13 as follows. In accordance with the Revised Amendment Format, the status of all claims is presented below.

1. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode electrically separate from said substrate is arranged in plasma spaced between the discharge electrode and the substrate in the vacuum vessel, and a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, wherein a voltage lower than the potential of plasma is applied to the auxiliary electrode to avoid discharge and to form the deposited film while controlling generation of hydrogen radicals.

2. (Cancelled)

3. (Original) The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 80 V.

4. (Original) The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 60 V.

5. (Original) The deposited-film formation method according to claim 1, wherein when the periodically changing voltage is applied to the auxiliary electrode, a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage.

6. (Previously Presented) The deposited-film formation method according to claim 1, wherein a plurality of said auxiliary electrodes is arranged at least in a flow direction of the material gas.

7. - 8. (Cancelled)

9. (Original) The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from an edgeless and small electrode having a small area facing a substrate in the vacuum vessel.

10. (Previously Presented ) The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from a round bar which has a small diameter and which is made of a high strength material of a high melting point metal.

11. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode electrically separate from said substrate is arranged in plasma spaced between the discharge electrode and the substrate in the vacuum vessel, a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode so that a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage to accelerate electrons at

minimum voltage with minimal effect on the plasma, thereby forming the deposited film and controlling generation of hydrogen radicals.

12. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode electrically separate from said substrate is arranged in plasma spaced between the discharge electrode and the substrate in the vacuum vessel, a high-frequency power of 1 MHz to 200 MHz is applied to the discharge electrode, and a high-frequency power of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, wherein a voltage lower than the potential of plasma is applied to the auxiliary electrode to avoid discharge, thereby forming the deposited film and controlling generation of hydrogen radicals.

13. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode electrically separate from said substrate is arranged in plasma spaced between the discharge electrode and the substrate in the vacuum vessel, a periodic electric field having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, and only electrons are energized without energizing ions to discompose a hydrogen gas and generate hydrogen radicals to provide a voltage lower than the potential of plasma to avoid discharge, thereby forming the deposited film and controlling the generation of the hydrogen radicals.

14. - 27. (Cancelled)